# POST METAL ETCH PHOTORESIST STRIP METHOD


## ABSTRACT

An improved method for removing a photoresist mask from an etched aluminum pattern after etching the pattern in a chlorine containing plasma has been developed. The method is a five step process, in which the first step is in a microwave generated plasma containing $O_2$ and $H_2O$; the second step is in a microwave generated plasma containing $O_2$ and $N_2$; the third step is in a microwave generated plasma containing $H_2O$; the fourth step is in a microwave generated plasma containing $O_2$ and $N_2$; and the fifth step is in a microwave generated plasma containing $H_2O$. The first step which initiates removal of photoresist while simultaneously beginning the passivation process causes residue-free removal of photoresist following etching of aluminum or aluminum-copper layers in chlorine bearing etchants.


**Figure 4**